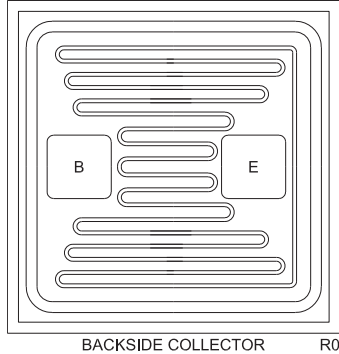


CP382X-CMPT3820

NPN - Low $V_{CE(SAT)}$ Transistor Die

1.0 Amp, 60 Volt

The CP382X-CMPT3820 is a silicon NPN transistor designed for battery driven, handheld devices requiring high current and low $V_{CE(SAT)}$.



MECHANICAL SPECIFICATIONS:

Die Size	26 x 26 MILS
Die Thickness	5.9 MILS
Base Bonding Pad Area	5.5 x 5.5 MILS
Emitter Bonding Pad Area	5.5 x 5.5 MILS
Top Side Metalization	Al – 30,000Å
Back Side Metalization	AU – 9,000Å
Scribe Alley Width	1.77 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	25,536

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	1.0	A
Peak Collector Current	I_{CM}	2.0	A
Continuous Base Current	I_B	300	mA
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

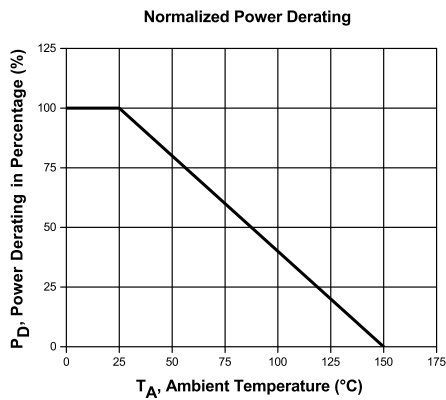
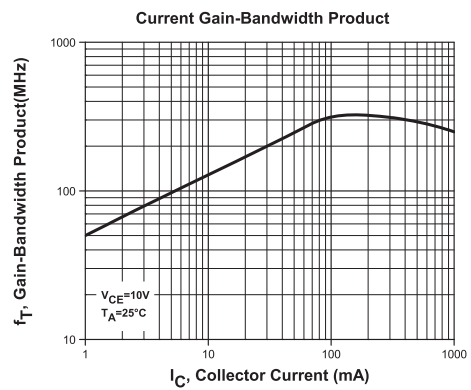
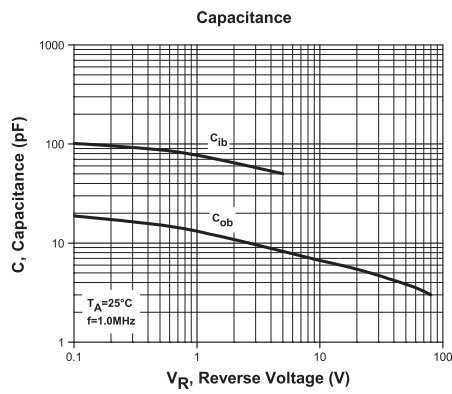
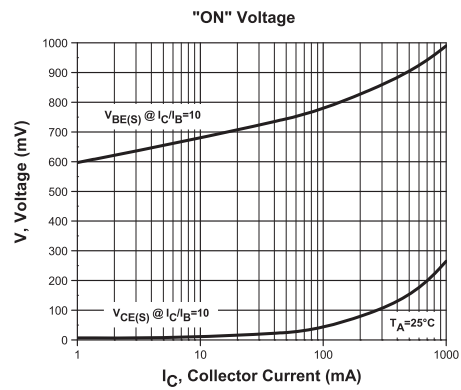
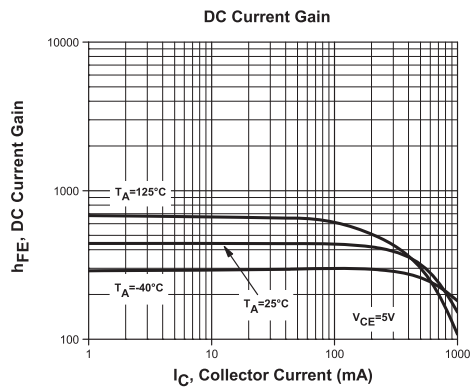
ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=60\text{V}$		100	nA
I_{EBO}	$V_{EB}=5.0\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	80		V
BV_{CEO}	$I_C=10\text{mA}$	60		V
BV_{EBO}	$I_E=100\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=1.0\text{mA}$		0.115	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.15	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		0.28	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=50\text{mA}$		1.1	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$		0.9	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	200		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=500\text{mA}$	200		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$	100		
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}$	150		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		10	pF

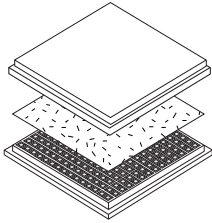
R0 (19-January 2017)

CP382X-CMPT3820

Typical Electrical Characteristics



BARE DIE PACKING OPTIONS



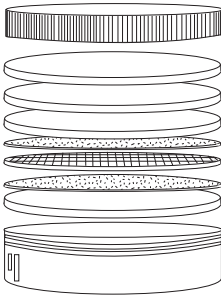
BARE DIE IN TRAY (WAFFLE) PACK

CT: Singulated die in tray (waffle) pack.

(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes).

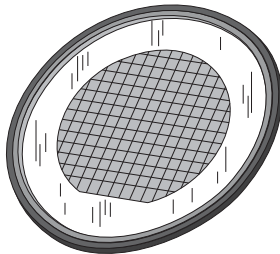
(example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked.

(example: CP211-PART NUMBER-WN)

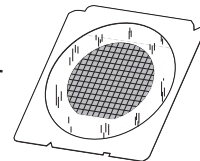


SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring, 100% tested with reject die inked.

(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



R1 (10-February 2017)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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